

Vishay Semiconductors

AAP Gen 7 (TO-240AA) Power Modules Thyristor/Thyristor, 75 A



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PRIMARY CHARACTERISTICS					
I _{T(AV)}	75 A				
Туре	Modules - thyristor, standard				
Package	AAP Gen 7 (TO-240AA)				

MECHANICAL DESCRIPTION

The AAP Gen 7 (TO-240AA), new generation of AAP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- · High voltage
- Industrial standard package



- · Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{T(AV)}	85 °C	75				
I _{T(RMS)}		115	Α			
ı	50 Hz	1300	A			
I _{TSM}	60 Hz	1360				
l²t	50 Hz	8.45	kA ² s			
1-1	60 Hz	7.68	KA-S			
I ² √t		84.5	kA²√s			
V _{RRM}	Range	400 to 1600	V			
T _{Stg}		-40 to +125	°C			
T _J		-40 to +125	°C			



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 125 °C mA			
	04	400	500	400				
VS-VSK.71	08	800	900	800	15			
12		1200	1300	1200	15			
	16	1600	1700	1600				

ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current	I _{T(AV)}	180° conduction	180° conduction, half sine wave, T _C = 85 °C			۸
Maximum continuous RMS on-state current		DC			115	Α
Maximum continuous AMS on-state current	I _{T(RMS)}	T _C			80	°C
		t = 10 ms	No voltage		1300	
Maximum peak, one-cycle non-repetitive	١.,	t = 8.3 ms	reapplied	Sinusoidal half wave,	1360	Α
on-state current	I _{TSM}	t = 10 ms	100 % V _{RRM}	initial $T_J = T_J$ maximum	1093	A
		t = 8.3 ms	reapplied	0 0	1140	
		t = 10 ms	No voltage		8.45	kA ² s
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied	Initial $T_J = T_J$ maximum	7.68	
	1-1	t = 10 ms	100 % V _{RRM}		5.97	
		t = 8.3 ms	reapplied		5.45	
Maximum I ² √t for fusing	I ² √t ⁽¹⁾		t = 0.1 ms to 10 ms, no voltage reapplied T _{.1} = T _{.1} maximum			kA²√s
Mariana	V (2)	Low level (3)	T T		0.96	.,
Maximum value of threshold voltage	V _{T(TO)} (2)	High level (4)	I J = I J maxin	$T_J = T_J$ maximum		V
Maximum value of on-state	(2)	Low level (3)	T T		3.28	0
slope resistance	r _t ⁽²⁾	High level (4)	$T_J = T_J$ maximum		2.86	mΩ
Maximum on-state voltage drop	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$ $T_J = 25 ^{\circ}C$		1.72	V	
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25 ^{\circ}\text{C}$, from 0.67 V_{DRM} , $I_{TM} = \pi x I_{T(AV)}$, $I_g = 500 \text{mA}$, $t_r < 0.5 \mu\text{s}$, $t_p > 6 \mu\text{s}$			150	A/µs
Maximum holding current	I _H	-	T _J = 25 °C, anode supply = 6 V, resistive load, gate open circuit			mA
Maximum latching current	ΙL	T _J = 25 °C, and	ode supply = 6 \	/, resistive load	400	

Notes

 $^{^{(1)}}$ I^2t for time $t_x = I^2 \sqrt{t} \ x \ \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

^{(3) 16.7 %} x π x $I_{AV} < I < \pi$ x I_{AV}

 $^{^{(4)}~}I>\pi~x~I_{AV}$



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TRIGGERING						
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS		UNITS	
Maximum peak gate power	P _{GM}			12	W	
Maximum average gate power	P _{G(AV)}			3.0	VV	
Maximum peak gate current	I _{GM}			3.0	Α	
Maximum peak negative gate voltage	- V _{GM}			10		
		T _J = - 40 °C	Anode supply = 6 V resistive load	4.0	V	
Maximum gate voltage required to trigger	V _{GT}	T _J = 25 °C		2.5		
		T _J = 125 °C		1.7		
		T _J = - 40 °C		270	mA	
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150		
		T _J = 125 °C	- resistive load	80		
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V	
Maximum gate current that will not trigger	I _{GD}	$T_J = 125 ^{\circ}\text{C}$, rated V_{DR}	_M applied	6	mA	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 125 °C, gate open circuit	15	mA
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V
Maximum critical rate of rise of off-state voltage	dV/dt	T_J = 125 °C, linear to 0.67 V_{DRM}	1000	V/µs

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Junction operating and storage temperature range		T _J , T _{Stg}		-40 to +125	°C			
Maximum internal thermal resistar junction to case per leg	nce,	R _{thJC}	DC operation	0.29	°C/W			
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	C/VV			
Mounting torque ± 10 %	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm			
Wounting torque ± 10 %	busbar		3 hours to allow for the spread of the compound.	3	INIII			
Approximate weight				75	g			
Approximate weight				2.7	oz.			
Case style			JEDEC®	AAP Gen 7	(TO-240AA)			

△R CONDUCTION PER JUNCTION											
DEVICES	8	SINE HALF	WAVE CO	NDUCTION	N	RE	CTANGUL	AR WAVE C	CONDUCTION	NC	UNITS
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.71	0.052	0.062	0.079	0.116	0.197	0.037	0.064	0.085	0.121	0.200	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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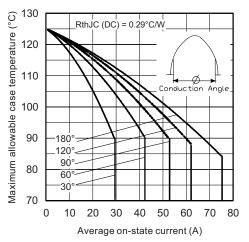


Fig. 1 - Current Ratings Characteristics

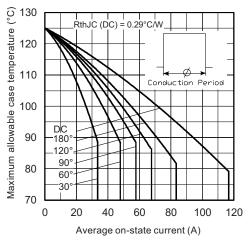


Fig. 2 - Current Ratings Characteristics

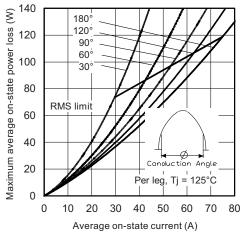


Fig. 3 - On-State Power Loss Characteristics

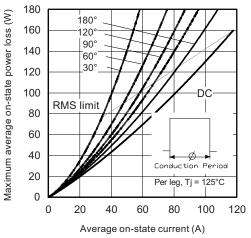
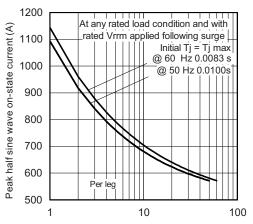


Fig. 4 - On-State Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

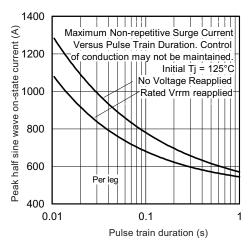


Fig. 6 - Maximum Non-Repetitive Surge Current

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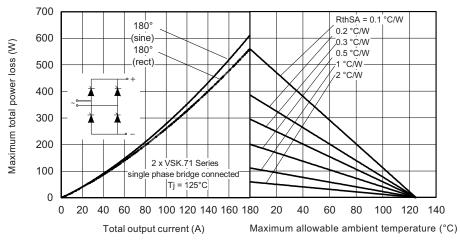


Fig. 7 - On-State Power Loss Characteristics

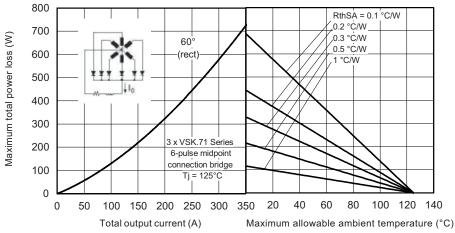


Fig. 8 - On-State Power Loss Characteristics

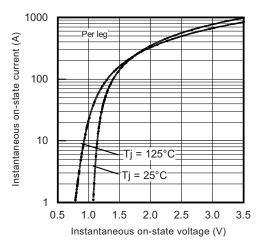


Fig. 9 - On-State Voltage Characteristics

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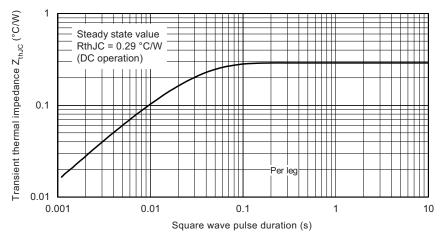


Fig. 10 - Thermal Impedance Z_{thJC} Characteristics

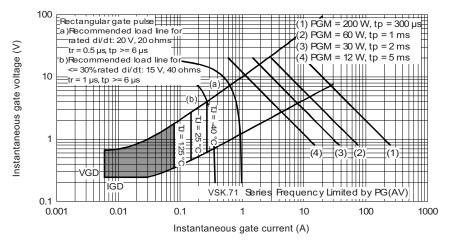
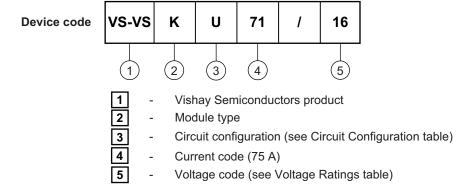


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172



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CIRCUIT CONFIGURATION	CIRCUIT CONFIGURATION								
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING							
Two SCRs common cathodes	U	VSKU (1) 1 2 (2) (3) (3) (3) (4) (5) (7) (6)							
Two SCRs common anodes	V	VSKV (1) 1 2 45 76 (3) (3) (3) (3) (4) (5) (7) (6)							

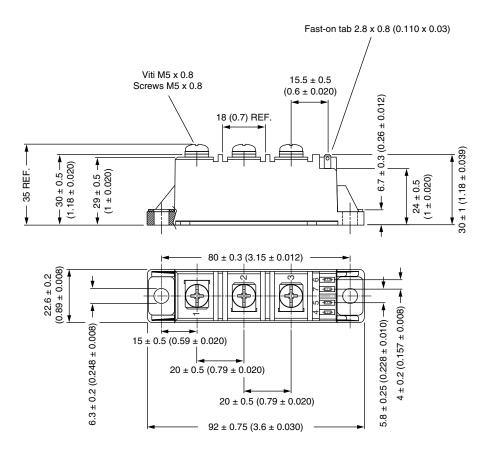
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95368



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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





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